

L Number	Hits	Search Text	DB	Time stamp
1	8760	((257/66) or (257/173) or (257/328) or (257/336) or (257/339) or (257/344) or (257/347) or (257/355) or (257/356) or (257/367) or (257/408)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:45
2	33111	soi or (silicon near2 insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:48
3	6075	buried near2 oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:48
4	1407	(dop\$3 near2 region\$1) near3 (first and second and third)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:49
5	1194164	concentration	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:50
6	3802	(soi or (silicon near2 insulator)) and (buried near2 oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:50
7	48	((soi or (silicon near2 insulator)) and (buried near2 oxide)) and ((dop\$3 near2 region\$1) near3 (first and second and third))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:50
8	30	((soi or (silicon near2 insulator)) and (buried near2 oxide)) and ((dop\$3 near2 region\$1) near3 (first and second and third)) and concentration	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:50
9	10	((257/66) or (257/173) or (257/328) or (257/336) or (257/339) or (257/344) or (257/347) or (257/355) or (257/356) or (257/367) or (257/408)).CCLS.) and (((soi or (silicon near2 insulator)) and (buried near2 oxide)) and ((dop\$3 near2 region\$1) near3 (first and second and third))) and concentration	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:50
-	5	(("5482871" or ("5926703" or ("6232163" or ("6352882" or ("6407428"))).PN.	USPAT	2004/07/13 18:43
-	11	("4656731" "4697198" "4829018" "4927779" "5185535" "5294821" "5359219" "5440161" "5506436" "5736435" "5780236").PN.	USPAT	2004/07/13 18:37
-	3	5926703.URPN.	USPAT	2004/07/13 18:39
-	8437	((257/66) or (257/173) or (257/328) or (257/336) or (257/339) or (257/344) or (257/347) or (257/355) or (257/356) or (257/367) or (257/408)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:45
-	30909	soi or (silicon near2 insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:48
-	5641	buried near2 oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:48

-	1328	((dop\$3 near2 region) near3 (first and second and third))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:48
-	1158168	concentration	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:49
-	3479	((soi or (silicon near2 insulator)) and (buried near2 oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:04
-	45	((soi or (silicon near2 insulator)) and (buried near2 oxide)) and ((dop\$3 near2 region) near3 (first and second and third))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:04
-	28	((soi or (silicon near2 insulator)) and (buried near2 oxide)) and ((dop\$3 near2 region) near3 (first and second and third))) and concentration	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:04
-	9	((soi or (silicon near2 insulator)) and (buried near2 oxide)) and ((dop\$3 near2 region) near3 (first and second and third))) and concentration) and (((257/66) or (257/173) or (257/328) or (257/336) or (257/339) or (257/344) or (257/347) or (257/355) or (257/356) or (257/367) or (257/408)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:05
-	19	((soi or (silicon near2 insulator)) and (buried near2 oxide)) and ((dop\$3 near2 region) near3 (first and second and third))) and concentration) not (((soi or (silicon near2 insulator)) and (buried near2 oxide)) and ((dop\$3 near2 region) near3 (first and second and third))) and concentration) and (((257/66) or (257/173) or (257/328) or (257/336) or (257/339) or (257/344) or (257/347) or (257/355) or (257/356) or (257/367) or (257/408)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:07
-	26	((soi or (silicon near2 insulator)) and (buried near2 oxide)) and ((dop\$3 near2 region) near3 (first and second and third))) not (((soi or (silicon near2 insulator)) and (buried near2 oxide)) and ((dop\$3 near2 region) near3 (first and second and third))) and concentration) not (((soi or (silicon near2 insulator)) and (buried near2 oxide)) and ((dop\$3 near2 region) near3 (first and second and third))) and concentration) and (((257/66) or (257/173) or (257/328) or (257/336) or (257/339) or (257/344) or (257/347) or (257/355) or (257/356) or (257/367) or (257/408)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:10
-	9238	bulk near3 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:10
-	36	((bulk near3 substrate) near5 "17")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:11

-	79	(bulk near3 substrate) and ((dop\$3 near2 region) near3 (first and second and third))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/13 19:11
-	1	((dop\$3 near2 region) near3 (first and second and third))near5 bulk near3 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/13 19:18
-	2	((dop\$3 near2 region) near3 (first and second and third))same bulk near3 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/13 19:14
-	79	((dop\$3 near2 region) near3 (first and second and third))and bulk near3 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/13 19:14
-	3	((dop\$3 near2 region) near3 (first and second and third))near5 bulk	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/13 19:20
-	0	(dop\$3 near2 region) near5 (bulk near3 substrate) same (high near3 concentrat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/13 19:47
-	10	(dop\$3 near2 region) near5 (bulk near3 substrate) and (high near3 concentrat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/13 19:48
-	7	(bulk near3 substrate) same ((high near3 concentrat\$3) near3 (channel or (channel near2 region)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/13 19:52
-	1738	((high near3 concentrat\$3) near3 (channel or (channel near2 region)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/13 19:53
-	442	((high near3 concentrat\$3) near3 (channel or (channel near2 region))) same dop\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/13 19:53
-	100	((high near3 concentrat\$3) near3 (channel or (channel near2 region))) same dop\$3) and (soi or (silicon near2 insulator))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/13 19:53
-	15	((high near3 concentrat\$3) near3 (channel or (channel near2 region))) same dop\$3) and (soi or (silicon near2 insulator))) and (bulk near3 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/13 19:55
-	85	((high near3 concentrat\$3) near3 (channel or (channel near2 region))) same dop\$3) and (soi or (silicon near2 insulator))) not (((high near3 concentrat\$3) near3 (channel or (channel near2 region))) same dop\$3) and (soi or (silicon near2 insulator))) and (bulk near3 substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/13 19:55
-	11	5599728.URPN.	USPAT	2004/07/13 19:59

-	23	("4697198" "4746960" "4784968" "4899202" "4948745" "4961165" "4985744" "4990983" "5072277" "5095348" "5102809" "5116771" "5125007" "5160989" "5212397" "5219768" "5243210" "5258318" "5264721" "5355011" "5359221" "5399525" "5413949") .PN.	USPAT	2004/07/13 19:59
-	24	5413949.URPN.	USPAT	2004/07/13 20:02
-	21	("4717683" "5217910" "5378650" "5413949" "5416033" "5548143" "5618740" "5658811" "5674760" "5753556" "5780328" "5792699" "5856225" "5893740" "5895954" "5930642" "5986314" "6005285" "6017808" "6025238" "6027978") .PN.	USPAT	2004/07/13 20:08